## Amendments to the Claims

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- (Cancelled)
- 2. (Previously Presented) The device as in Claim 56, wherein the packaged sen conductor is packaged in a ball grid array package.
- 3. (Previously Presented) The device as in Claim 56, wherein the unpackaged sen conductor die is a graphics processor.
- 4. (Previously Presented) The device as in Claim 56, wherein the packaged sen conductor is a memory.
- 5. (Previously Presented) The device as in Claim 56, wherein a plurality of pac aged semiconductors are attached to the package module.
- 6. (Previously Presented) The device as in Claim 56, wherein the unpackaged serr conductor die is wire bonded to the package module.
- 7. (Currently amended) The device as in Claim [1] 57, wherein the unpackaged sem conductor die is wire bonded to the package module.
- 8. (Previously Presented) The device as in Claim 56, wherein attached includes surf ce-mount technology reflow.
- 9. (Previously Presented) The device as in Claim 56, wherein the encapsulated stru ture has a footprint greater than the footprint of the unpackaged semiconductor die.
- 10. (Currently amended) The device in Claim [1] <u>56</u>, wherein the unpackaged sem conductor die is underfilled.
- 11. (Previously Presented) The device as in Claim 56, wherein the footprint size of the ackage module is one of 35 mm × 35 mm, 31 mm × 31 mm, 27 mm × 27 mm, 37.5 mm × 37.4 mm, 40 mm × 40 mm, 42 mm × 42 mm, or 42.5 mm × 42.5 mm.
  - 12. (Previously Presented) The device as in Claim 56, further including a heat sink.

- 13. (Previously Presented) The device in Claim 12, wherein a top surface of the unit ickaged semiconductor die and a top surface of the packaged semiconductor are of the packaged semiconductor are of the package module matter to the package matter to the package module matter to the package matter to the p
- (Currently amended) The device as in Claim [12] <u>59</u>, further including a shim postioned over the unpackaged semiconductor die such that a top of the shim and a top surface of the packaged semiconductor are of substantially equal distance from a surface of the multi-die mo ule.
  - 15. (Cancelled).
- 16. (Previously Presented) The device as in Claim 56, wherein the packaged sen iconductor die is packaged in a ball grid array package.
- 17. (Previously Presented) The device as in Claim 57, wherein a plurality of pactaged memory are attached to the package module.
- 18. (Previously Presented) The device as in Claim 57, wherein directly attached inc ides the graphics processing die being wire bonded to the package module.
- 19. (Currently amended) The device as in Claim [15] <u>57</u>, wherein directly attached inc ides flip-chip attachment.
- 20. (Previously Presented) The device as in Claim 57, wherein attached includes sur ice-mount technology reflow.
  - 21. (Cancelled)
- 22. (Currently amended) The device as in Claim [15] <u>57</u>, wherein the graphics-pro essing die is underfilled.
- 23. (Previously Presented) The device as in Claim 57, wherein the standard package size include one of 35 mm × 35 mm, 31 mm × 31 mm, 27 mm × 27 mm, 37.5 mm × 37.5 mm, 40 mm × 40 mm, 42 mm × 42 mm, or 42.5 mm.

- 24. (Previously presented) The device as in Claim 57, further including a heat sinks
- 25. (Previously Presented) The device in Claim 24, wherein a top-surface of the tree gra hics-processor die and a top surface of the packaged memory are of substantially equal transfer of the package module.
- 26. (Currently Amended) The device as in Claim [24] <u>57</u>, further including a shim postioned on top of the graphics-processor die, such that a top of the shim and a top surface of the packaged memory are of substantially equal distance from a surface of the package module.
  - 27. (Cancelled)
  - 28. (Cancelled)
  - 29. (Cancelled)
  - 30. (Cancelled)
  - 31. (Cancelled)
  - 32. (Cancelled)
  - 33. (Cancelled)
  - 34. (Cancelled)
  - 35. (Cancelled)
  - 36. (Cancelled)
  - 37. (Cancelled)
  - 38. (Cancelled)
  - 39. (Cancelled)
  - 40. (Cancelled)
- 41. (Previously Presented) The device as in Claim 9, wherein the encapsulated ser iconductor die forms a substantially rectangular structure on the package module.

- gra hics-processing die forms a substantially rectangle structure on the package modules a substantially rectangle structure on the package modules a substantially rectangle structure.
  - 43. (Cancelled)
- 44. (Previously Presented) The multi-die module as in Claim 58, further including a sec nd packaged semiconductor die mounted on the first surface of the substrate.
- 45. (Previously Presented) The multi-die module as in Claim 58, further including a plu ality of unpackaged semiconductor die mounted on the first surface of the substrate.
- 46. (Previously Presented) The multi-die module as in Claim 58, wherein the unlackaged semiconductor die is mounted to the first surface of the substrate by wire bonding.
- 47. (Previously Presented) The multi-die module as in Claim 58, wherein the encepsulating structure is further comprised of an encapsulating material including epoxy, metal car or silicon coatings.
- 48. (Previously Presented) The multi-die module as in Claim 58, further including a hea sink.
  - 49. (Cancelled)
- 50. (Currently Amended) The multi-die module as in Claim [43] <u>59</u>, wherein the unjuckaged semiconductor die is under[]filled.
  - (Cancelled)
- 52. (Currently Amended) The multi-die as in Claim [51] 56, further including a shim postioned over the surface of the unpackaged semiconductor die such [as] that a\_top of the shim and the top surface of the packaged semiconductor die are of substantially equal distance from the first surface of the substrate.
- 53. (Previously Presented) The multi-die module as in Claim 58, wherein the unjuckaged semiconductor die is a graphics processor.

- pac aged semiconductor die is a memory.
  - 55. (Cancelled)
  - 56. (Previously Presented) A device comprising:

    a package module including a substrate having a standard package footprint;

    an unpackaged semiconductor die directly attached to the package module, the unpackaged semiconductor die encapsulated onto the package module in a structure having a planar top surface; and

a packaged semiconductor die having a top surface and attached to the package module:

wherein the planar top surface of the encapsulated structure and the top surface of the packaged semiconductor die are of equal distance from the substrate.

- 57. (Previously Presented) A device comprising:
  - a package module sized to be interchangeable with standard package sizes;
- a graphics-processing die directly attached to the package module, the graphicsprocessing die encapsulated on the package module in a structure having a planar top surface; and

a packaged memory die having a top surface and attached to the package module; wherein the planar top surface of the encapsulated structure and the top surface of the packaged memory die are of equal distance from the package module.

- 58. (Previously Presented) A multi-die module, comprising:
  - a substrate having a first surface and a second surface;

an unpackaged semiconductor die mounted to the first surface of the substrate, the semiconductor die encapsulated in a structure having a planar top surface; and

a packaged semiconductor die having a top surface and mounted on the firstconductor of the substrate;

wherein the planar top surface of the encapsulated structure and the top surface of the packaged semiconductor die are of equal distance from the substrate.

59. (Currently Amended) A multi-die module, comprising: a substrate having a first surface;

an unpackaged semiconductor die mounted to the first surface of the substrate, the semiconductor die encapsulated in a structure <u>having a planar top surface</u>; and

a packaged semiconductor die mounted on the first surface of the substrate wherein the encapsulating structure is further comprised of an encapsulating material of a metal cap wherein a planar top surface of the encapsulated structure and the top surface of the packaged semiconductor die are of equal distance from the substrate.

- 60. (Currently Amended) The device of Claim 56 further including a planar heat sink add sted to engage the encapsulated structure and the top surface of the packaged semiconductor.
  - 61. (New) A multi-die module, comprising:a substrate having a first surface;

an unpackaged semiconductor die mounted to the first surface of the substrate, the semiconductor die encapsulated in a structure having a planar top surface; and

a packaged semiconductor die having a top surface and mounted on the first surface of the substrate:

wherein the planar top surface of the encapsulated structure and the top surface of the packaged semiconductor die are of equal distance from the substrate.

(New) The device as in Claim 61, wherein the unpackaged semiconductor die is uncerfilled.

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